

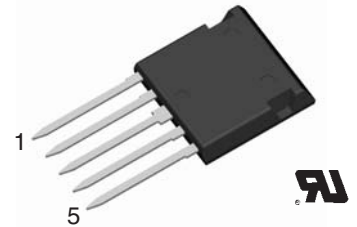
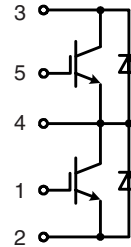
NPT³ IGBT

Phaseleg Topology
in ISOPLUS i4-PAC™

$$I_{C25} = 33 \text{ A}$$

$$V_{CES} = 1200 \text{ V}$$

$$V_{CE(sat)typ} = 2.4 \text{ V}$$



IGBTs

Symbol	Conditions	Maximum Ratings	
V_{CES}	$T_{VJ} = 25^{\circ}\text{C to } 150^{\circ}\text{C}$	1200	V
V_{GES}		± 20	V
I_{C25}	$T_C = 25^{\circ}\text{C}$	33	A
I_{C90}	$T_C = 90^{\circ}\text{C}$	20	A
I_{CM} V_{CEK}	$V_{GE} = \pm 15 \text{ V}; R_G = 68 \Omega; T_{VJ} = 125^{\circ}\text{C}$ RBSOA, Clamped inductive load; $L = 100 \mu\text{H}$	40 V_{CES}	A
t_{SC} (SCSOA)	$V_{CE} = 900\text{V}; V_{GE} = \pm 15 \text{ V}; R_G = 68 \Omega; T_{VJ} = 125^{\circ}\text{C}$ non-repetitive	10	μs
P_{tot}	$T_C = 25^{\circ}\text{C}$	150	W

Symbol	Conditions	Characteristic Values ($T_{VJ} = 25^{\circ}\text{C}$, unless otherwise specified)		
		min.	typ.	max.
$V_{CE(sat)}$	$I_C = 20 \text{ A}; V_{GE} = 15 \text{ V}; T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$		2.4 2.8	V V
$V_{GE(th)}$	$I_C = 0.6 \text{ mA}; V_{GE} = V_{CE}$	4.5		6.5 V
I_{CES}	$V_{CE} = V_{CES}; V_{GE} = 0 \text{ V}; T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$		0.2	0.2 mA mA
I_{GES}	$V_{CE} = 0 \text{ V}; V_{GE} = \pm 20 \text{ V}$			200 nA
$t_{d(on)}$ t_r $t_{d(off)}$ t_f E_{on} E_{off}	Inductive load, $T_{VJ} = 125^{\circ}\text{C}$ $V_{CE} = 600 \text{ V}; I_C = 20 \text{ A}$ $V_{GE} = \pm 15 \text{ V}; R_G = 68 \Omega$		205 105 320 175 4.1 1.5	ns ns ns ns mJ mJ
C_{ies}	$V_{CE} = 25 \text{ V}; V_{GE} = 0 \text{ V}; f = 1 \text{ MHz}$		1.2	nF
Q_{Gon}	$V_{CE} = 600 \text{ V}; V_{GE} = 15 \text{ V}; I_C = 20 \text{ A}$		100	nC
R_{thJC} R_{thJH}	with heat transfer paste		1.2	0.8 K/W K/W

Features

- NPT³ IGBT
 - positive temperature coefficient of saturation voltage for easy paralleling
 - fast switching
 - short tail current for optimized performance in resonant circuits
- HiPerFRED™ diode
 - fast reverse recovery
 - low operating forward voltage
 - low leakage current
- ISOPLUS i4-PAC™ package
 - isolated back surface
 - low coupling capacity between pins and heatsink
 - enlarged creepage towards heatsink
 - application friendly pinout
 - low inductive current path
 - high reliability
 - industry standard outline
 - UL registered, E 72873

Applications

- single phaseleg
 - buck-boost chopper
- H bridge
 - power supplies
 - induction heating
 - four quadrant DC drives
 - controlled rectifier
- three phase bridge
 - AC drives
 - controlled rectifier

Diodes

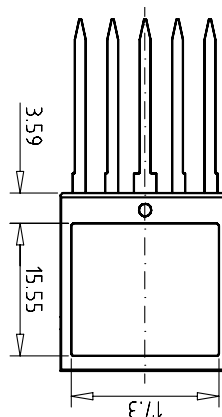
Symbol	Conditions	Maximum Ratings	
I_{F25}	$T_C = 25^\circ\text{C}$	25	A
I_{F90}	$T_C = 90^\circ\text{C}$	15	A

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
V_F	$I_F = 20\text{ A}; T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$	2.5 1.9	3.0	V V
I_{RM} t_{rr}	$I_F = 15\text{ A}; di_F/dt = -400\text{ A}/\mu\text{s}; T_{VJ} = 125^\circ\text{C}$ $V_R = 600\text{ V}; V_{GE} = 0\text{ V}$	16 130		A ns
R_{thJC} R_{thCH}	(per diode) with heat transfer paste	3.6		2.3 K/W K/W

Component

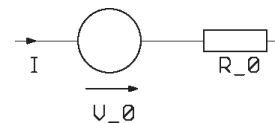
Symbol	Conditions	Maximum Ratings	
T_{VJ} T_{stg}		-55...+150 -55...+125	$^\circ\text{C}$ $^\circ\text{C}$
V_{ISOL}	$I_{ISOL} \leq 1\text{ mA}; 50/60\text{ Hz}$	2500	V~
F_C	mounting force with clip	20...120	N

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
C_p	coupling capacity between shorted pins and mounting tab in the case		40	pF
d_S, d_A	pin - pin	1.7		mm
d_S, d_A	pin - backside metal	5.5		mm
Weight		9		g



Equivalent Circuits for Simulation

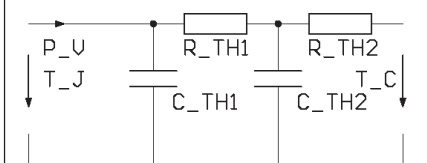
Conduction



IGBT (typ. at $V_{GE} = 15\text{ V}; T_J = 125^\circ\text{C}$)
 $V_o = 1.09\text{ V}; R_o = 85\text{ m}\Omega$

Free Wheeling Diode (typ. at $T_J = 125^\circ\text{C}$)
 $V_o = 1.3\text{ V}; R_o = 32\text{ m}\Omega$

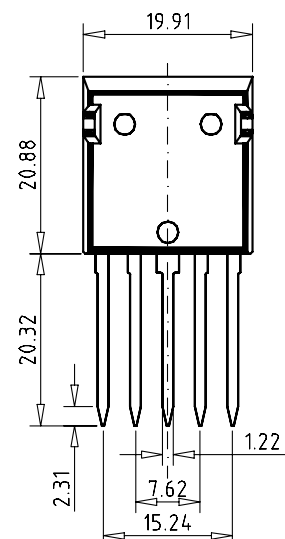
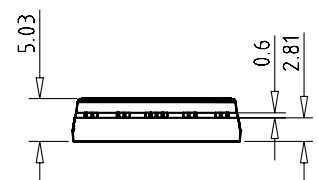
Thermal Response



IGBT (typ.)
 $C_{th1} = 0.049\text{ J/K}; R_{th1} = 0.15\text{ K/W}$
 $C_{th2} = 0.133\text{ J/K}; R_{th2} = 0.65\text{ K/W}$

Free Wheeling Diode (typ.)
 $C_{th1} = 0.021\text{ J/K}; R_{th1} = 0.63\text{ K/W}$
 $C_{th2} = 0.052\text{ J/K}; R_{th2} = 1.67\text{ K/W}$

Dimensions in mm (1 mm = 0.0394")



IXYS reserves the right to change limits, test conditions and dimensions.

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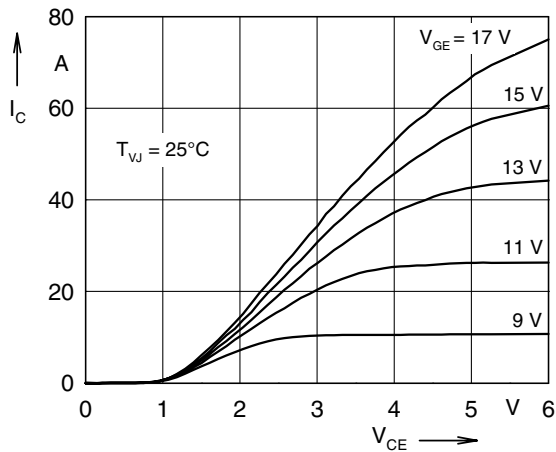


Fig. 1 Typ. output characteristics

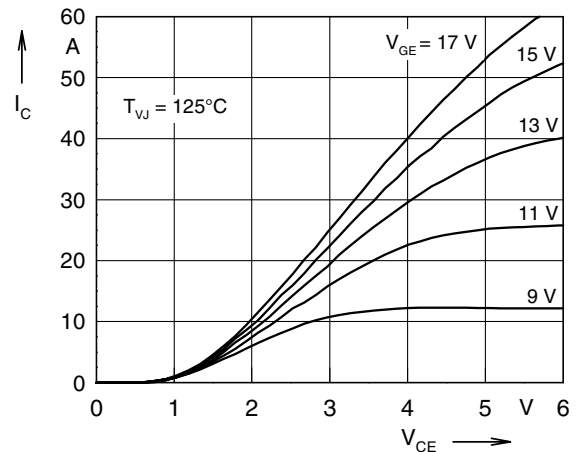


Fig. 2 Typ. output characteristics

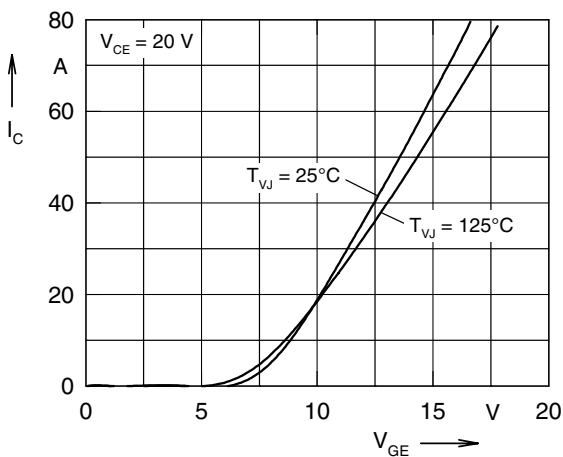


Fig. 3 Typ. transfer characteristics

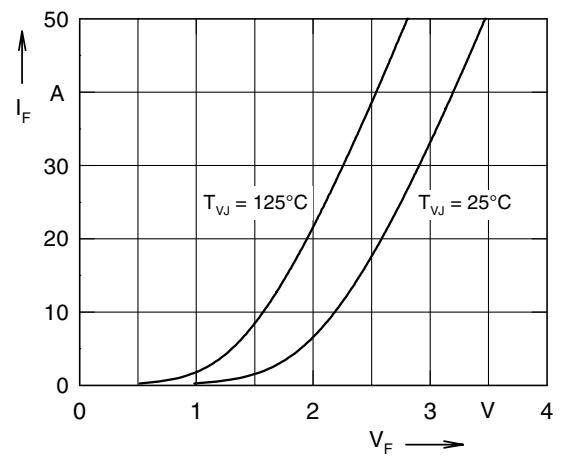


Fig. 4 Typ. forward characteristics of free wheeling diode

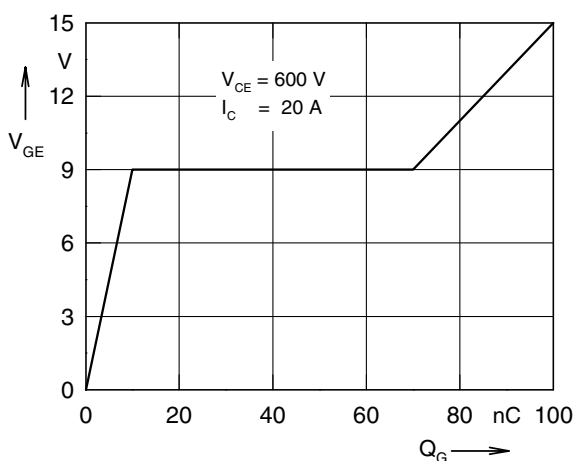


Fig. 5 Typ. turn on gate charge

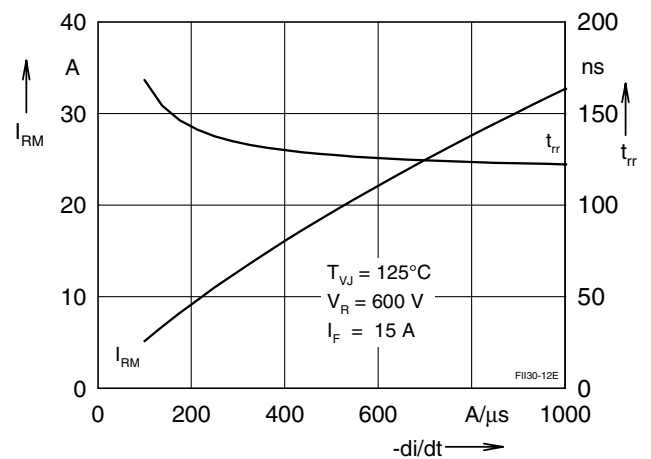


Fig. 6 Typ. turn off characteristics of free wheeling diode

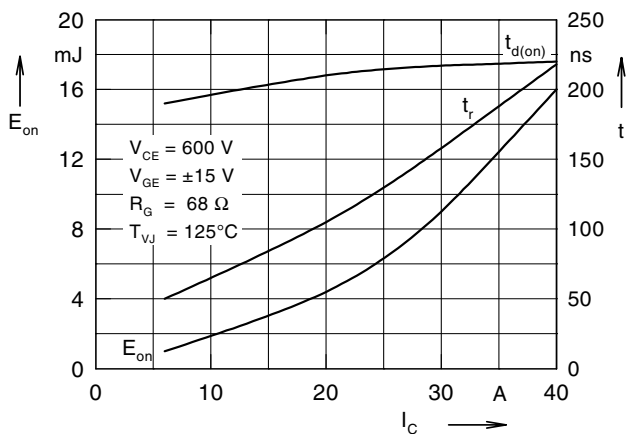


Fig. 7 Typ. turn on energy and switching times versus collector current

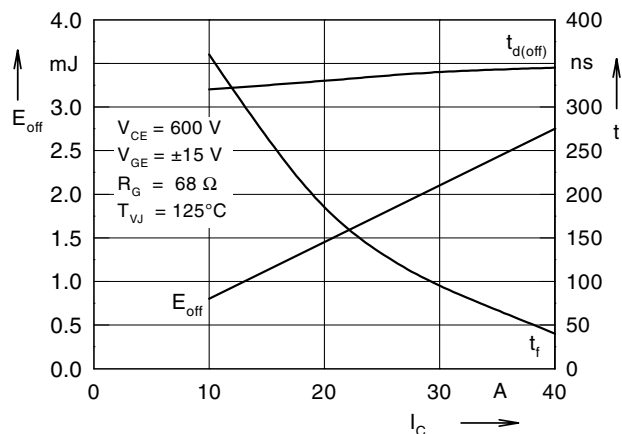


Fig. 8 Typ. turn off energy and switching times versus collector current

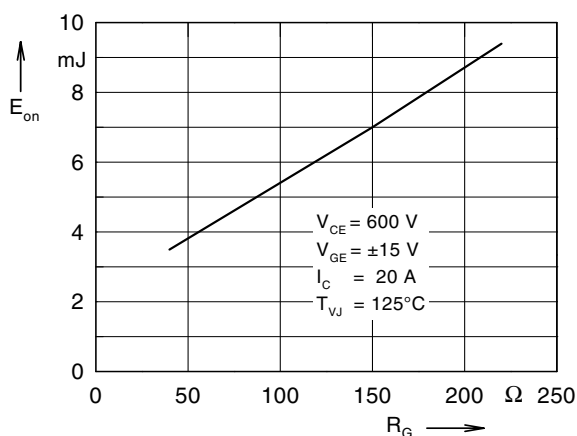


Fig. 9 Typ. turn on energy vs gate resistor

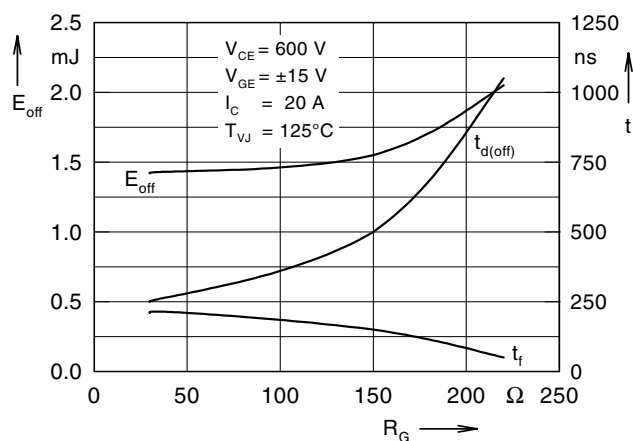


Fig. 10 Typ. turn off energy and switching times versus gate resistor

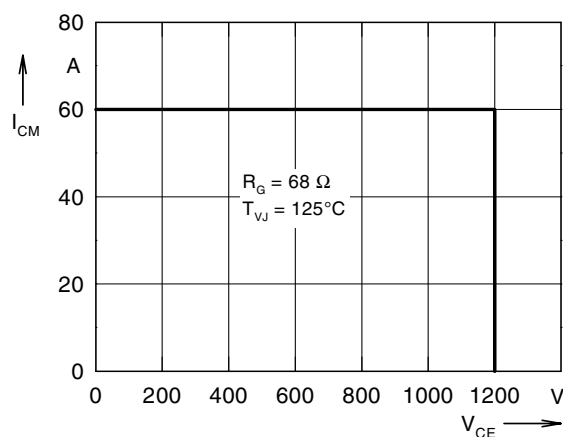


Fig. 11 Reverse biased safe operating area RBSOA

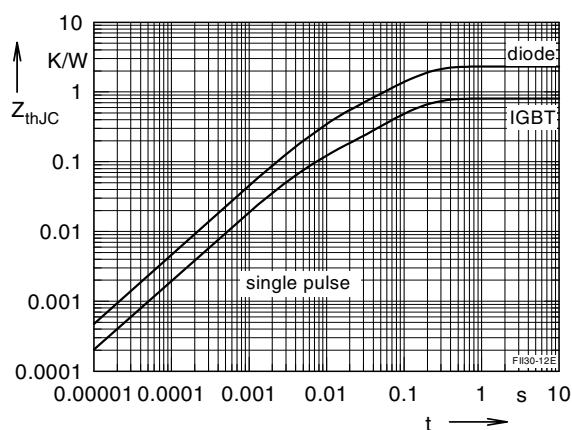


Fig. 12 Typ. transient thermal impedance